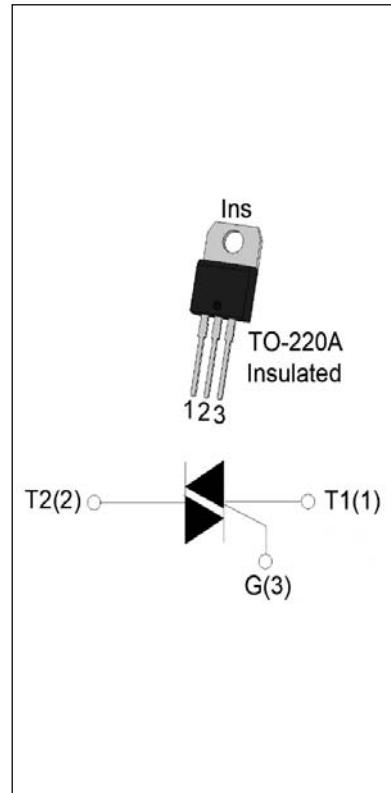


**DESCRIPTION:**

The JST20A-800BW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST20A-800BW snubberless triac is especially recommended for use on inductive loads. By using an internal ceramic pad, JST20A-800BW provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	20	A
$V_{DRM}/V_{RRM}$	800	V
$I_{GT\text{ I/II/III}}$	50/50/50	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	°C
Operating junction temperature range	$T_j$	-40-125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{DRM}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{RRM}$	800	V
RMS on-state current ( $T_c \leq 75^\circ\text{C}$ )	$I_{T(RMS)}$	20	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{TSM}$	200	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )		220	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	200	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ )	$dI/dt$	100	$\text{A}/\mu\text{s}$
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )	$I_{GM}$	4	A
Average gate power dissipation ( $T_j=125^\circ\text{C}$ )	$P_{G(AV)}$	0.5	W

Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25^\circ\text{C}$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	3.8	kV

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12\text{V}$ $R_L=33\Omega$	I - II - III	MAX.	50	mA
$V_{GT}$		I - II - III	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	I - II - III	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	I - III	MAX.	60	mA
		II		80	
$I_H$	$I_T=500\text{mA}$		MAX.	60	mA
$dV/dt$	$V_D=540\text{V}$ Gate Open $T_j=125^\circ\text{C}$		MIN.	2000	V/ $\mu\text{s}$
$(dI/dt)c$	$(dV/dt)c=20\text{V}/\mu\text{s}$ $T_j=125^\circ\text{C}$		MIN.	25	A/ms
$t_{on}$	$I_G=80\text{mA}$ $I_A=400\text{mA}$ $I_R=40\text{mA}$ $T_j=25^\circ\text{C}$	TYP.		10	$\mu\text{s}$
$t_{off}$				70	

**STATIC CHARACTERISTICS**

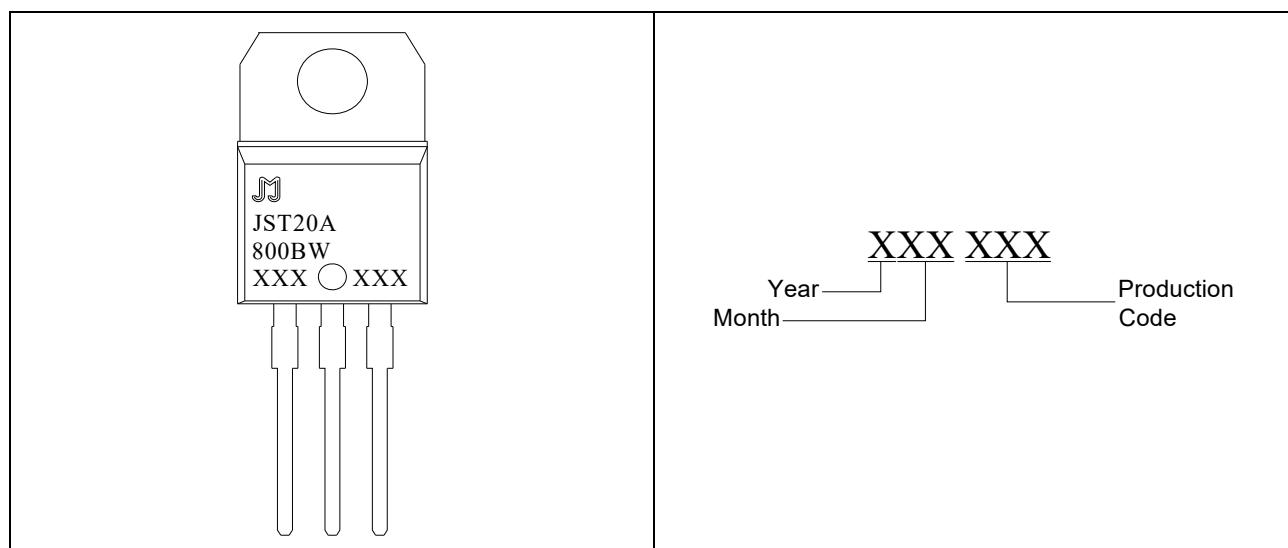
Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=28\text{A}$	$t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.4
$V_{TO}$	Threshold voltage		$T_j=125^\circ\text{C}$	0.75
$R_D$	Dynamic resistance		$T_j=125^\circ\text{C}$	20
$I_{DRM}$	$V_D=V_{DRM}$	$V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5
$I_{RRM}$			$T_j=125^\circ\text{C}$	1

**THERMAL RESISTANCES**

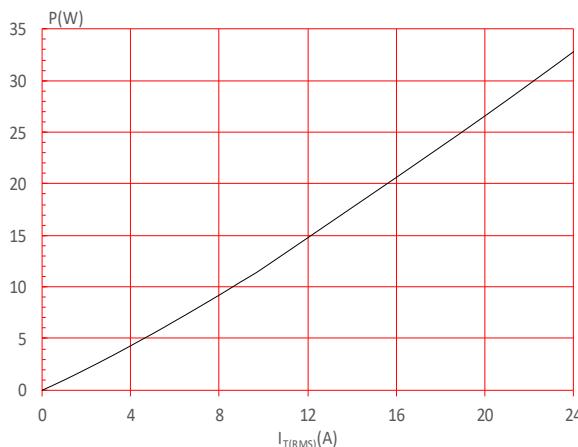
Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.9	$^\circ\text{C/W}$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^\circ\text{C/W}$

**ORDERING INFORMATION**

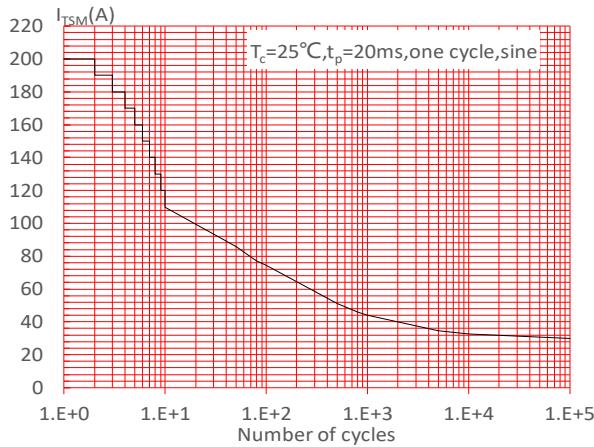
<u>J</u>	<u>ST</u>	<u>20</u>	<u>A</u>	<u>-800</u>	<u>BW</u>
JieJie Microelectronics Co., Ltd.					
	Triacs				
		<u>I<sub>T(RMS)</sub>:20A</u>			
			<u>A:TO-220A(Ins)</u>		
				<u>800:V<sub>DRM</sub> / V<sub>RRM</sub> ≥ 800V</u>	<u>BW:IGT1-3 ≤ 50mA</u>

**MARKING**

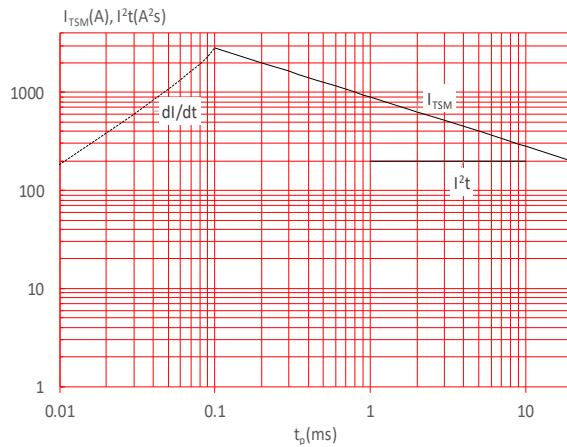
**FIG.1** Maximum power dissipation versus RMS on-state current



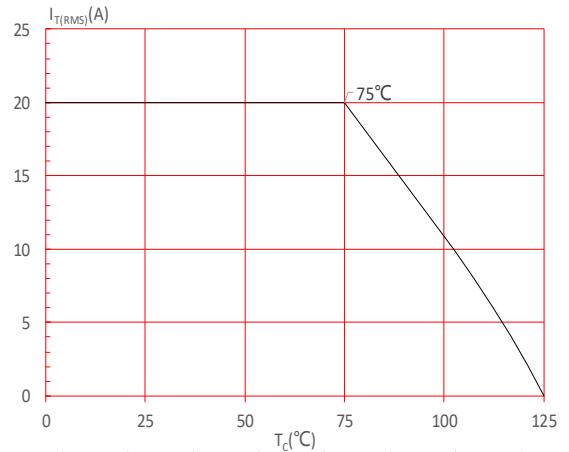
**FIG.3:** Surge peak on-state current versus number of cycles



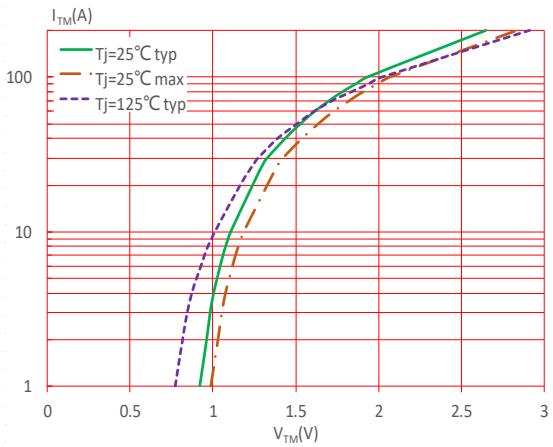
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $dI/dt < 100\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

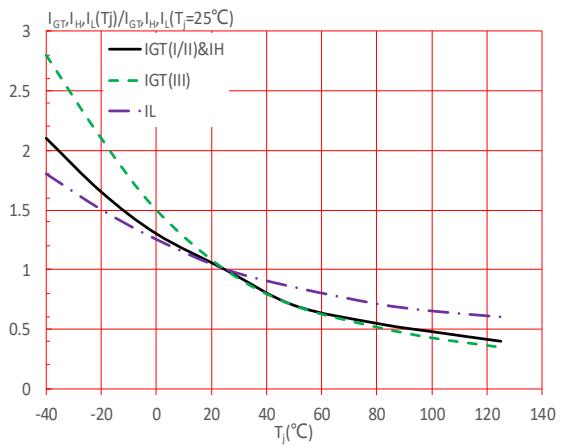
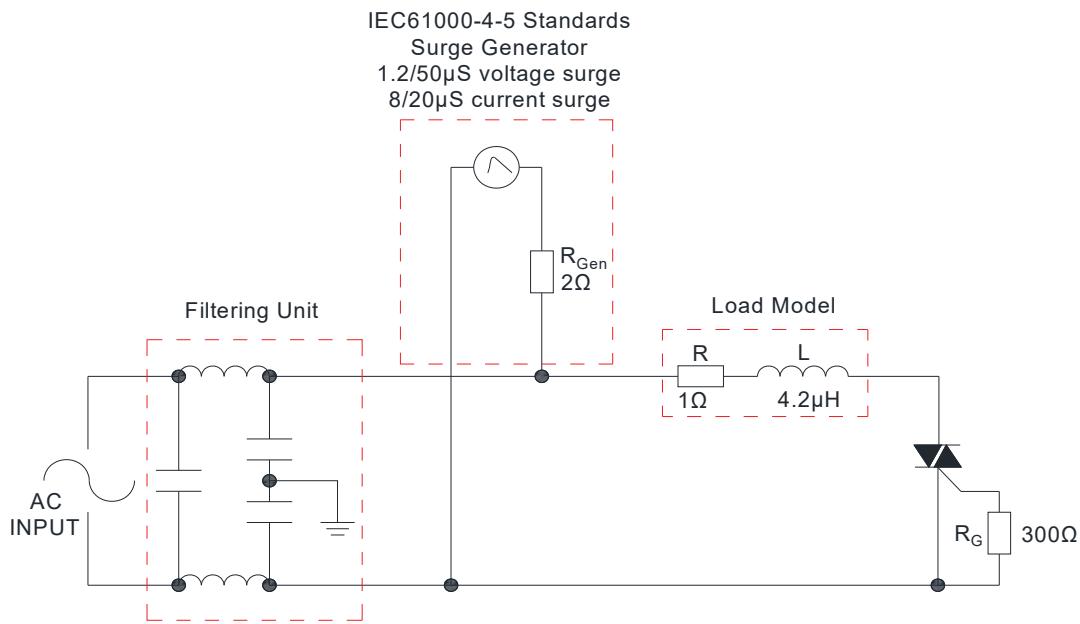


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



## SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie

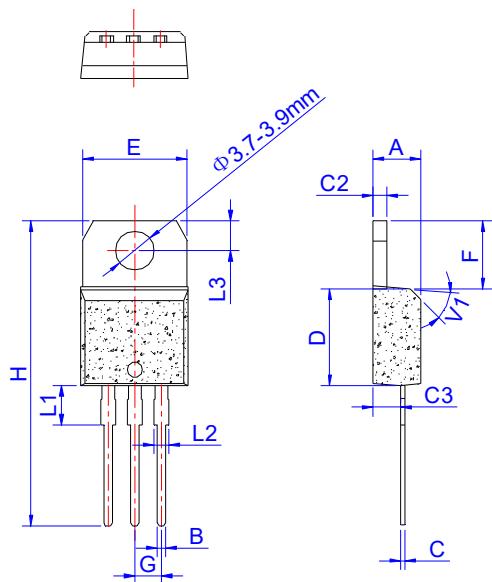
**ORDERING INFORMATION**

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I -II-III			
<b>JST20A-800BW</b>	<b>800</b>	<b>50</b>	<b>TO-220A(Ins)</b>	<b>50</b>	<b>Tube</b>

**Document Revision History**

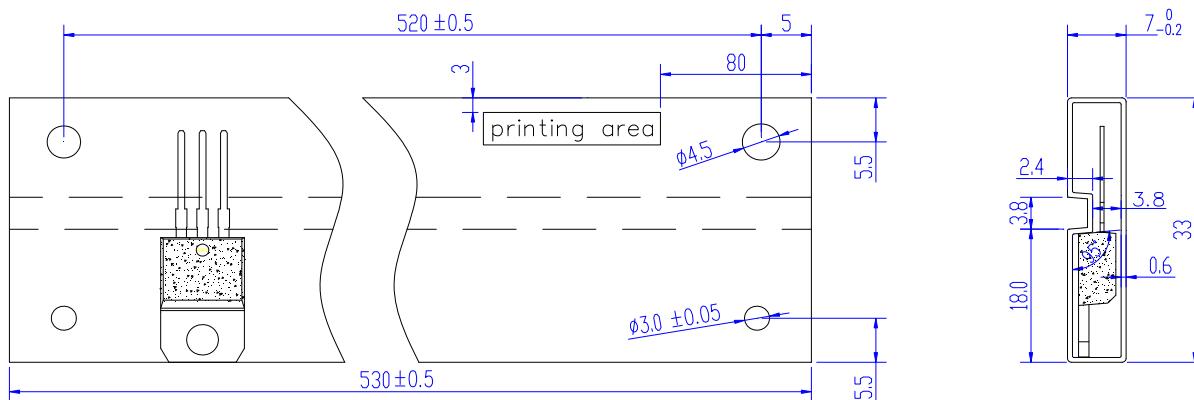
Date	Revision	Changes
Apr.12, 2023	A.1.0	Last updated

## PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.25		6.85	0.246		0.270
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	3.45		4.05	0.136		0.159
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

## DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220A	TUBE	50	1,000	5,000

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